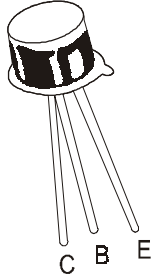


PNP SILICON PLANAR EPITAXIAL TRANSISTORS

BCY70 , 71, 72



**TO-18
Metal Can Package**

General Purpose Industrial Applications.

ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	BCY70	BCY71	BCY72	UNIT
Collector Emitter Voltage	V_{CEO}	40	45	25	V
Collector Base Voltage	V_{CBO}	50	45	30	V
Emitter Base Voltage	V_{EBO}	5	5	5	V
Collector Current Continuous	I_C		200		mA
Collector Current Peak	I_{CM}		200		mA
Power Dissipation @Ta=25°C	P_D		350		mW
Derate Above 25°C			2		mW/°C
Operating Storage and Junction Temperature Range	T_{stg}		-65 to +200		°C

THERMAL RESISTANCE

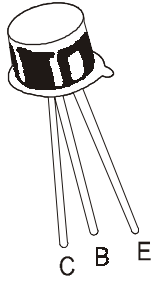
Junction to Ambient	$R_{th(j-a)}$		500		°C/W
Junction to Case	$R_{th(j-c)}$		150		°C/W

ELECTRICAL CHARACTERISTICS (Ta=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	VALUE			UNIT
			BCY70	BCY71	BCY72	
Collector Emitter Breakdown Voltage	BV_{CEO}	$I_C=1mA, I_B=0$	>40	>45	>25	V
Collector Base Breakdown Voltage	BV_{CBO}	$I_C=100\mu A, I_E=0$	>50	>45	>30	V
Emitter Base Breakdown Voltage	BV_{EBO}	$I_E=100\mu A, I_C=0$	>5	>5	>5	V
Collector Cut off Current	I_{CBO}	$V_{CB}=40V, I_E=0$	<10	<50		nA
		$V_{CB}=25V, I_E=0$			<50	nA
		$V_{CB}=40V, I_E=0$	<0.5	<2.0		µA
		$T_j = 100^\circ C$				
		$V_{CB}=25V, I_E=0$			<2	µA
		$T_j = 100^\circ C$				
		$V_{CB}=V_{CBO} \text{ MAX}, I_E=0$	<500	<500	<500	nA
Collector Cut off Current	I_{CEX}	$V_{CE} =50V, V_{EB} =3V$	<20			nA

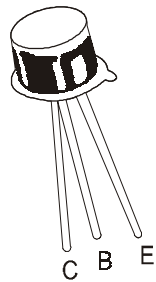
PNP SILICON PLANAR EPITAXIAL TRANSISTORS

BCY70 , 71, 72



TO-18
Metal Can Package

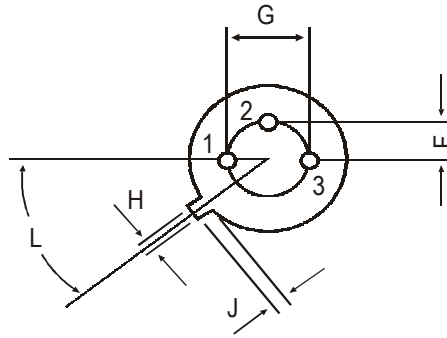
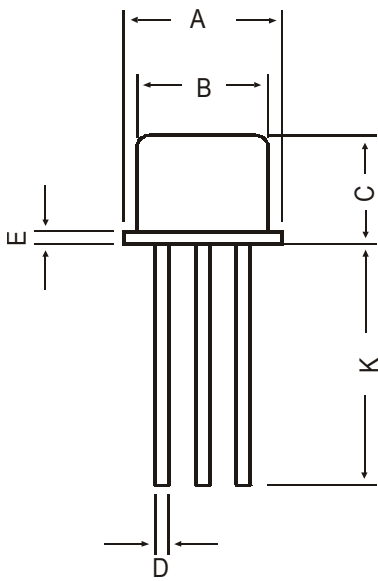
DESCRIPTION	SYMBOL	TEST CONDITION	VALUE			UNIT
			MIN	TYP	MAX	
Emitter Cut off Current	I_{EBO}	$V_{EB}=4V, I_C=0$			10	nA
		$V_{EB}=4V, I_C=0,$ $T_j = 100^\circ C$			2	μA
		$V_{EB}=54V, I_C=0$			500	nA
DC Current Gain	h_{FE}	$I_C=10\mu A, V_{CE}=1V$	60			
		$I_C=100\mu A, V_{CE}=1V$	80			
		$I_C=1mA, V_{CE}=1V$	100			
		BCY70 BCY71 $I_C=10mA, V_{CE}=1V$	100		400	
		$I_C=50mA, V_{CE}=1V$	45			
Collector Emitter Saturation Voltage	$V_{CE(Sat)}$	$I_C=10mA, I_B=1mA$			250	mV
		$I_C=50mA, I_B=5mA$			500	mV
Base Emitter Saturation Voltage	$V_{BE(Sat)}$	$I_C=10mA, I_B=1mA$	600		900	V
		$I_C=50mA, I_B=5mA$			1.2	V
<u>DYNAMIC CHARACTERISTICS</u>						
Transition Frequency	f_T	$I_C=10mA, V_{CE}=20V$ $f=100MHz$	250			MHz
		BCY71 $I_C=100\mu A, V_{CE}=20V$ $f=10.7MHz$	15			MHz
Collector Capacitance	C_c	$V_{CB}=10V, I_E=0, f=1MHz$			6.0	pF
Emitter Capacitance	C_e	$V_{EB}=1.0V, f=1MHz, I_C=0$			8.0	pF
Noise Figure	NF	$I_C=0.1mA, V_{CE}=5V$				
		BCY70, 72 BCY71 $R_s=2K\Omega, f=10Hz \text{ to } 10KHz$			6	dB
					2	dB
Input Impedance	h_{ie}	$I_C=10mA, V_{CE}=10V, f=1KHz$		4.0		$K\Omega$
Reverse Voltage Transfer Ratio	h_{re}	$I_C=10mA, V_{CE}=10V, f=1KHz$		2.1		$\times 10^{-4}$
Small Signal Current Gain	$ h_{fe} $	$I_C=10mA, V_{CE}=10V, f=1KHz$		325		
Out put Admittance	h_{oe}	$I_C=10mA, V_{CE}=10V, f=1KHz$		20		$\mu mhos$



TO-18
Metal Can Package

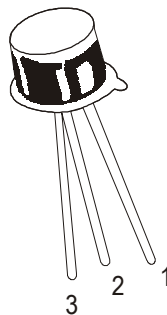
DESCRIPTION	SYMBOL	TEST CONDITION	VALUE			UNIT
			MIN	TYP	MAX	
SWITCHING CHARACTERISTICS						
Delay time	t_d	$I_C=10\text{mA}, I_{B\text{on}}=I_{B\text{off}}=1\text{mA}$			35	ns
Rise time	t_r	$I_C=10\text{mA}, I_{B\text{on}}=I_{B\text{off}}=1\text{mA}$			35	ns
Turn on Time	t_{on}	$I_C=10\text{mA}, I_{B\text{on}}=I_{B\text{off}}=1\text{mA}$			65	
Storage time	t_s	$I_C=10\text{mA}, I_{B\text{on}}=I_{B\text{off}}=1\text{mA}$			350	ns
Fall time	t_f	$I_C=10\text{mA}, I_{B\text{on}}=I_{B\text{off}}=1\text{mA}$			80	ns
Turn Off Time	t_{off}	$I_C=10\text{mA}, I_{B\text{on}}=I_{B\text{off}}=1\text{mA}$			420	ns

TO-18 Metal Can Package



All dimensions in mm.

DIM	MIN	MAX
A	5.24	5.84
B	4.52	4.97
C	4.31	5.33
D	0.40	0.53
E	—	0.76
F	—	1.27
G	—	2.97
H	0.91	1.17
J	0.71	1.21
K	12.70	—
L	45 DEG	



PIN CONFIGURATION

1. EMITTER
2. BASE
3. COLLECTOR

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-18	1K/polybag	350 gm/1K pcs	3" x 7.5" x 7.5"	5K	17" x 15" x 13.5"	80K	34 kgs

Disclaimer

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